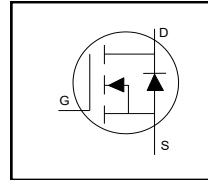


- Logic - Level Gate Drive
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



V_{DSS}	30V
R_{DS(on) max.}	0.006Ω
I_D	140A[Ⓞ]



G	D	S
Gate	Drain	Source

Description

Fifth Generation HEXFETs utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRL3803PbF	TO-220	Tube	50	IRL3803PbF


Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	140 [Ⓞ]	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	98 [Ⓞ]	
I _{DM}	Pulsed Drain Current ^①	470	
P _D @ T _C = 25°C	Maximum Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V _{GS}	Gate-to-Source Voltage	± 16	V
E _{AS}	Single Pulse Avalanche Energy ^②	610	mJ
I _{AR}	Avalanche Current ^①	71	A
E _{AR}	Repetitive Avalanche Energy ^①	20	mJ
dv/dt	Peak Diode Recovery dv/dt ^③	5.0	V/ns
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

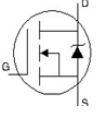
Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	0.75	°C/W
R _{θJC}	Case-to-Sink, Flat, Greased Surface	0.50	—	
R _{θJA}	Junction-to-Ambient	—	62	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.052	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.006	Ω	V _{GS} = 10V, I _D = 71A ^④
		—	—	0.009		V _{GS} = 4.5V, I _D = 59A ^④
V _{GS(th)}	Gate Threshold Voltage	1.0	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Trans conductance	55	—	—	S	V _{DS} = 25V, I _D = 71A
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 30V, V _{GS} = 0V
		—	—	250		V _{DS} = 24V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -16V
Q _g	Total Gate Charge	—	—	140	nC	I _D = 71A
Q _{gs}	Gate-to-Source Charge	—	—	41		V _{DS} = 24V
Q _{gd}	Gate-to-Drain Charge	—	—	78		V _{GS} = 4.5V, See Fig. 6 and 13 ^④
t _{d(on)}	Turn-On Delay Time	—	14	—	ns	V _{DD} = 15V
t _r	Rise Time	—	230	—		I _D = 71A
t _{d(off)}	Turn-Off Delay Time	—	29	—		R _G = 1.3Ω
t _f	Fall Time	—	35	—		R _D = 0.2Ω, See Fig. 10 ^④
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	5000	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	1800	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	880	—		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	140 ^⑤	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ^①	—	—	470		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 71A, V _{GS} = 0V ^④
t _{rr}	Reverse Recovery Time	—	120	180	ns	T _J = 25°C, I _F = 71A
Q _{rr}	Reverse Recovery Charge	—	450	680	nC	di/dt = 100A/μs ^④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S + L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig.11)
- ② V_{DD} = 15V, starting T_J = 25°C, L = 180μH, R_G = 25Ω, I_{AS} = 20A.(See Figure 12)
- ③ I_{SD} ≤ 71A, di/dt ≤ 130A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Calculated continuous current based on maximum allowable junction temperature; for recommended current- handling of the package refer to Design TIP # 93-4

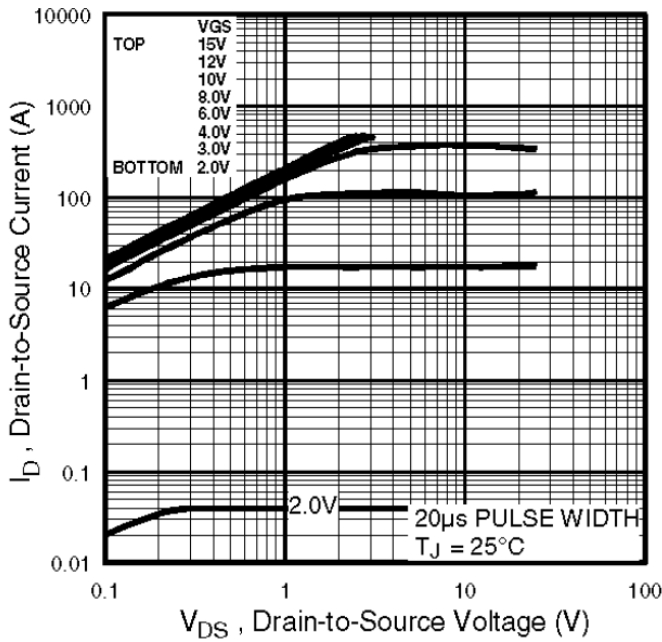


Fig. 1 Typical Output Characteristics
 $T_J = 25^\circ\text{C}$

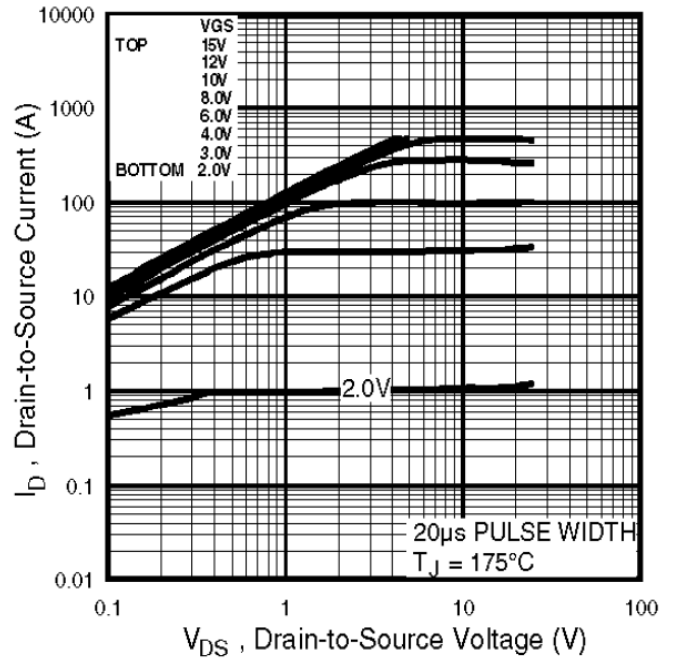


Fig. 2 Typical Output Characteristics
 $T_J = 175^\circ\text{C}$

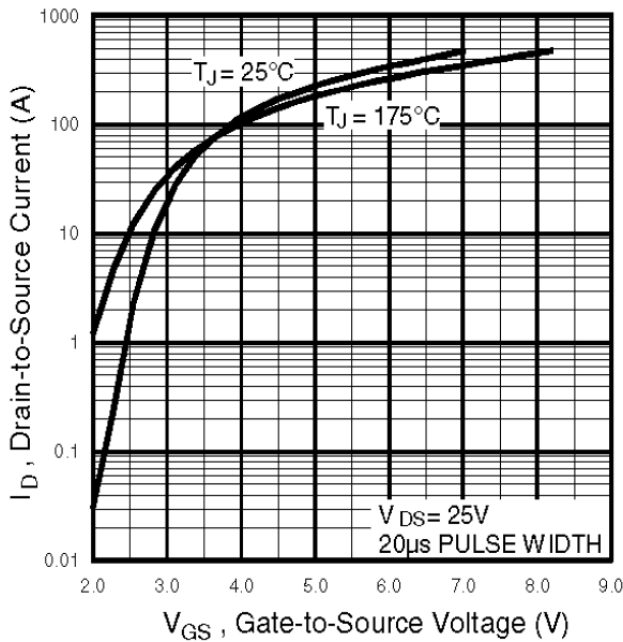


Fig. 3 Typical Transfer Characteristics

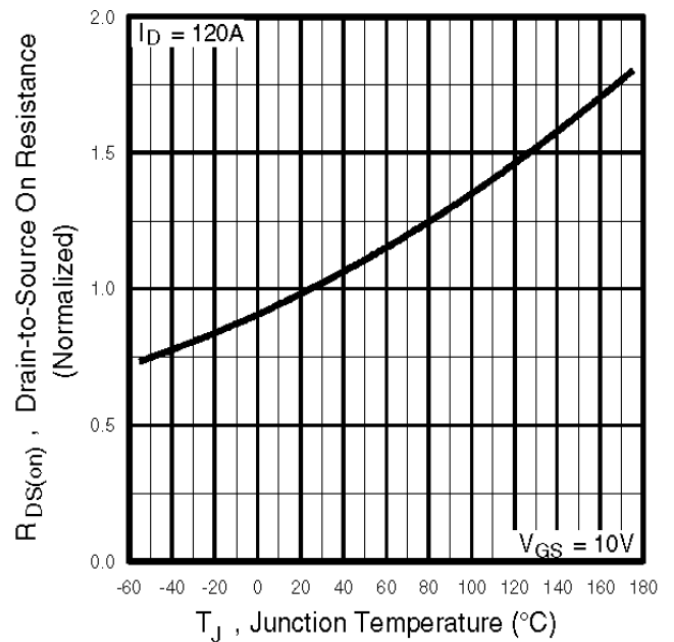


Fig. 4 Normalized On-Resistance
 vs. Temperature

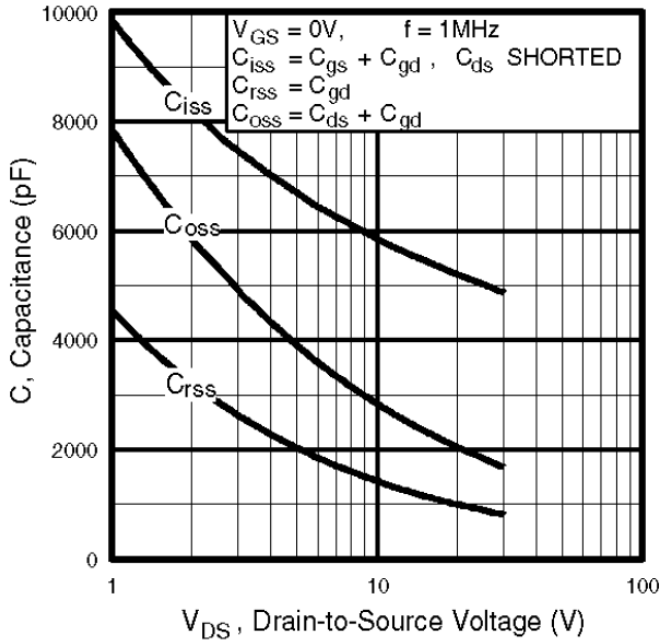


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

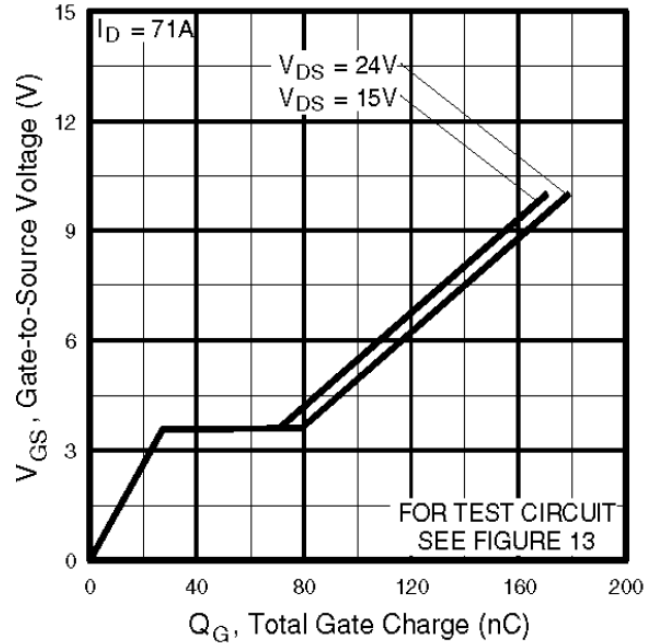


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

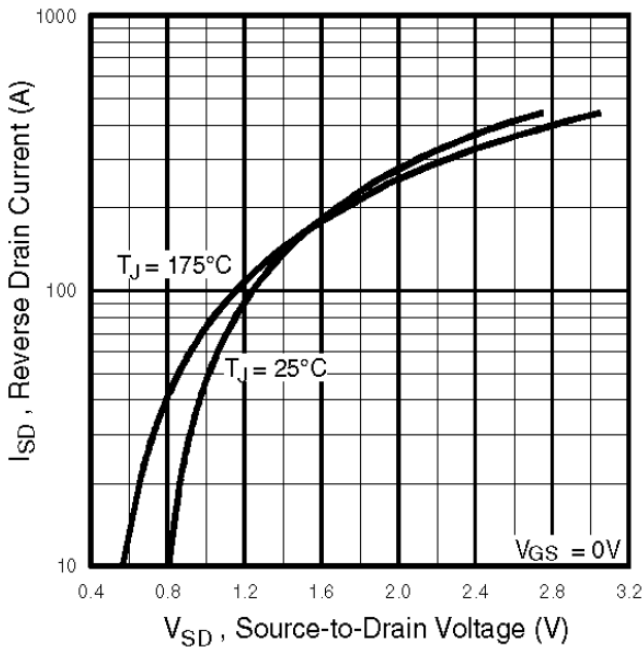


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

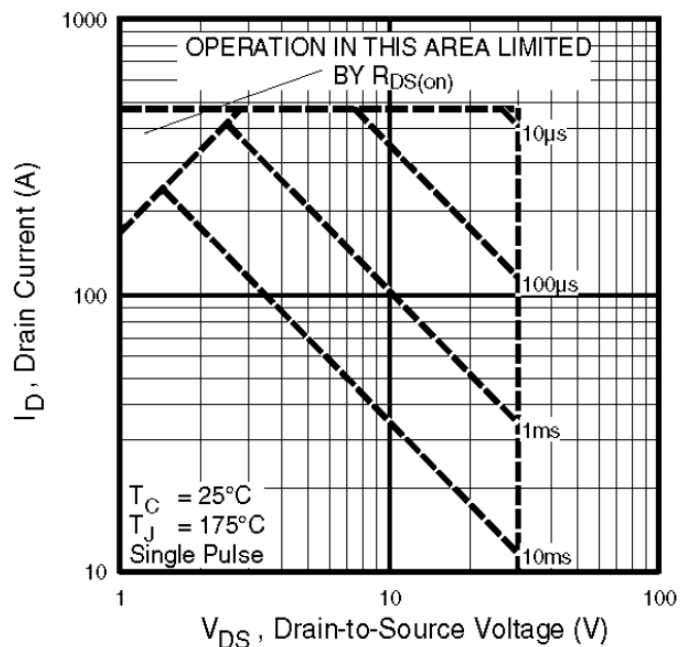
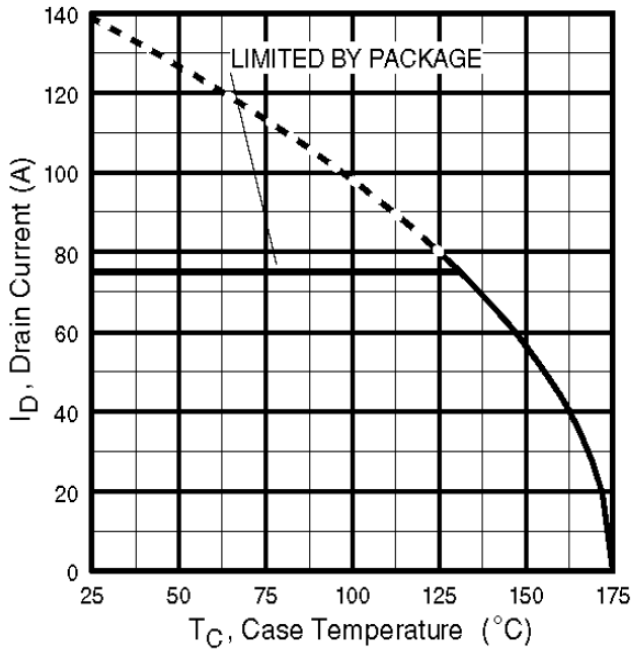
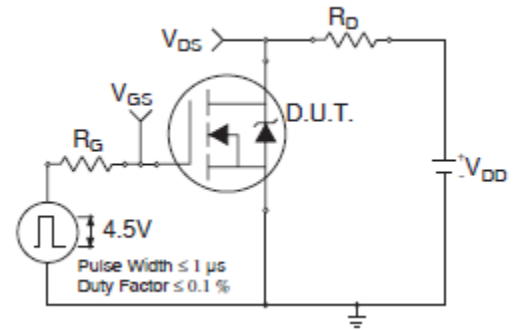
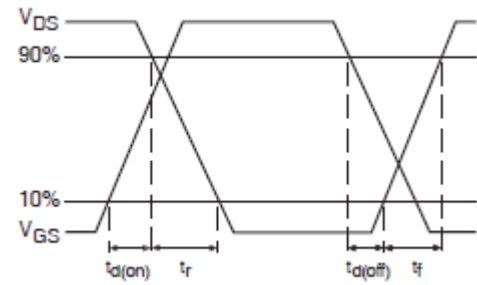
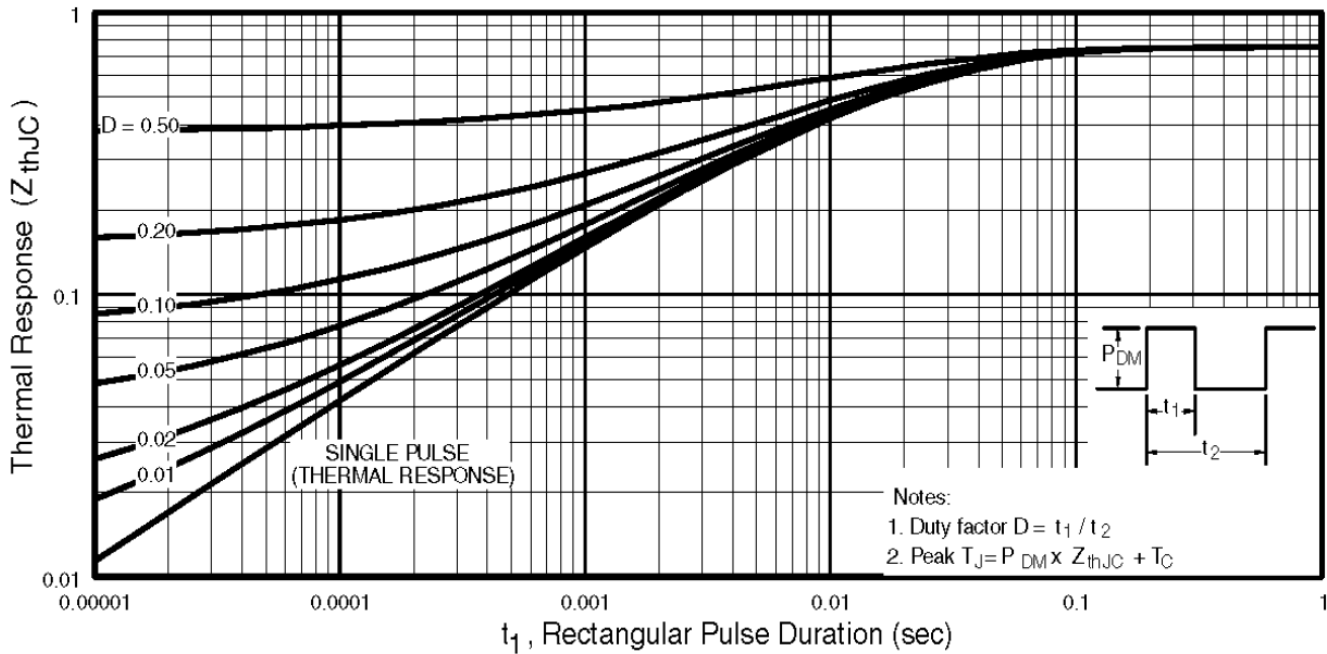
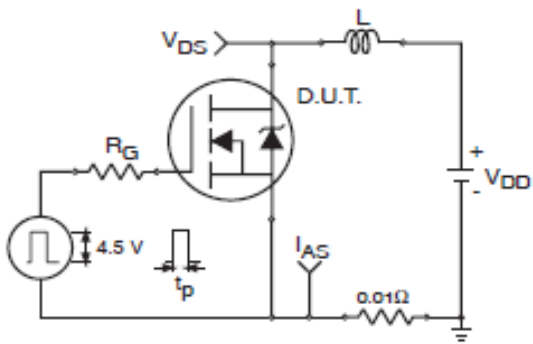
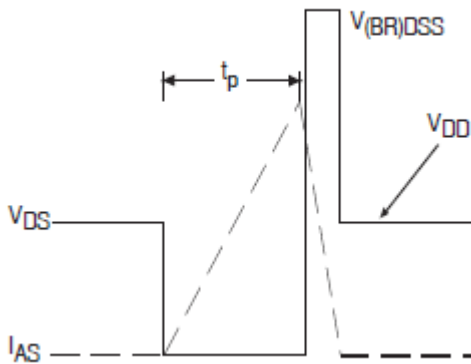
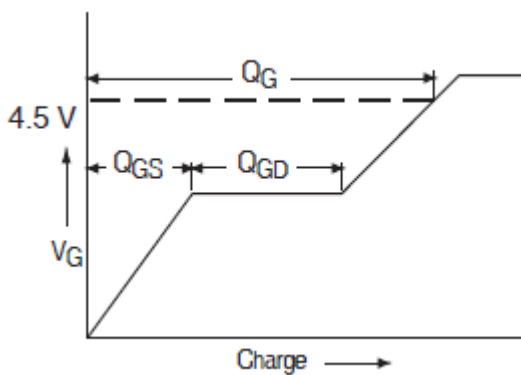
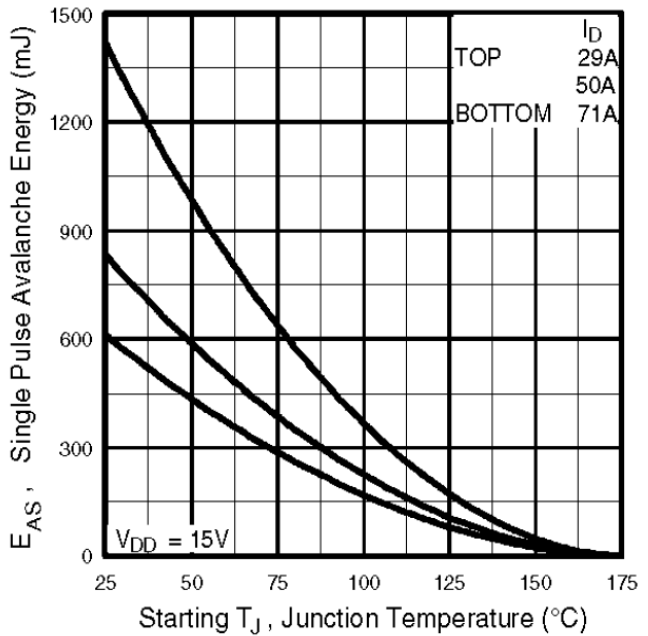
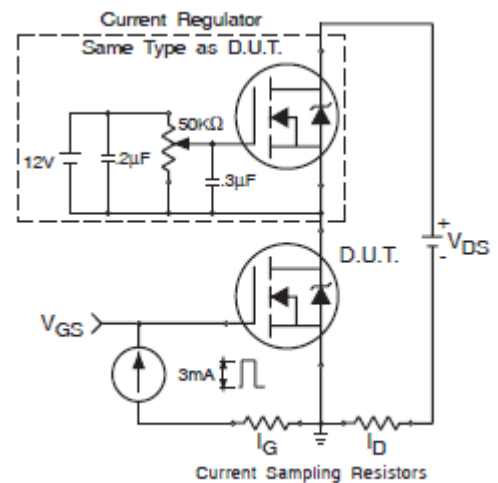
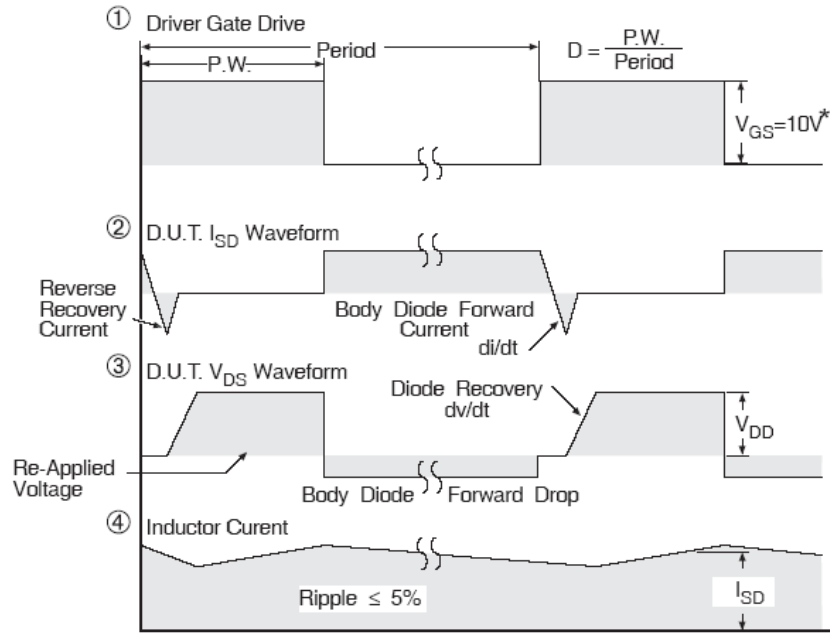
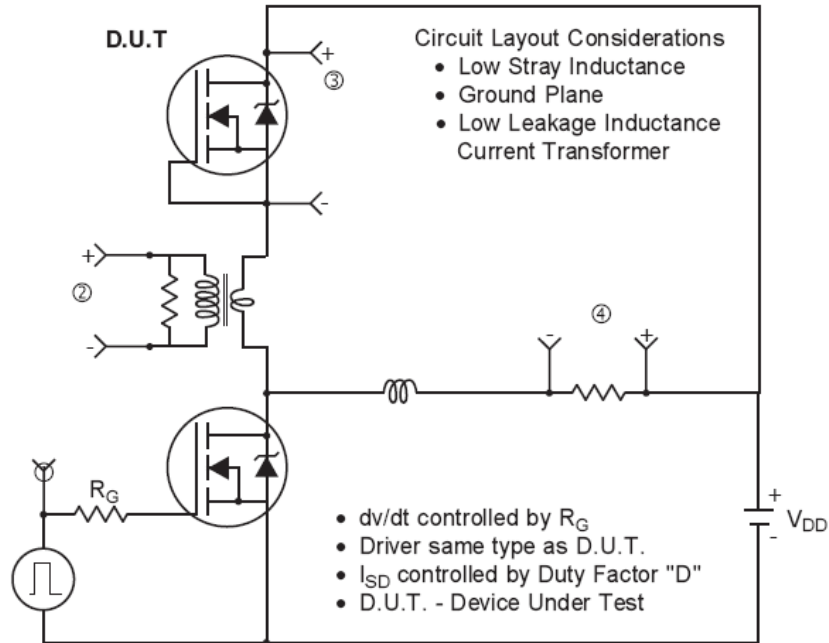


Fig 8. Maximum Safe Operating Area


Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10a. Switching Time Test Circuit

Fig 10b. Switching Time Waveforms

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

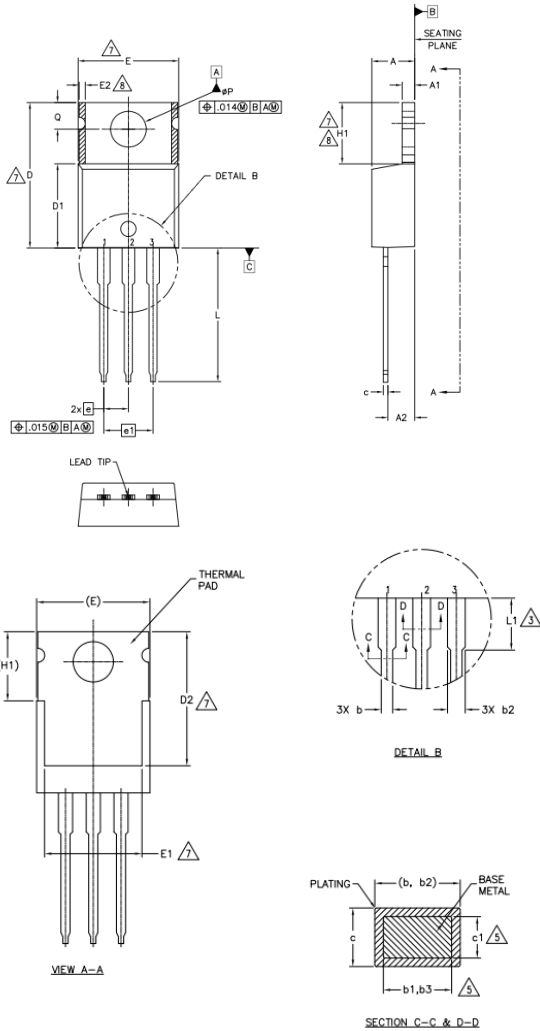

Fig 12a. Unclamped Inductive Test Circuit

Fig 12b. Unclamped Inductive Waveforms

Fig 13a. Gate Charge Waveform

Fig 12c. Maximum Avalanche Energy vs. Drain Current

Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power

TO-220 Package Outline (Dimensions are shown in millimeters (inches))

NOTES:

- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 6.- CONTROLLING DIMENSION : INCHES.
- 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

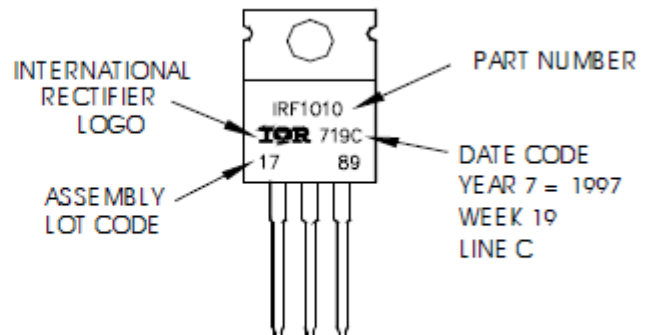
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	1.14	1.40	.045	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
ØP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

- LEAD ASSIGNMENTS**
- HEXFET**
- 1- GATE
 - 2- DRAIN
 - 3- SOURCE
- IGBTs, CoPACK**
- 1- GATE
 - 2- COLLECTOR
 - 3- EMITTER
- DIODES**
- 1- ANODE
 - 2- CATHODE
 - 3- ANODE

Note: For the most current drawing please refer to website at <http://www.irf.com/packaging>

TO-220 Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
 Note: "P" in assembly line position indicates "Lead-Free"



Note: For the most current drawing please refer to website at <http://www.irf.com/packaging>

Revision History

Date	Rev.	Comments
02/25/2021	2.1	<ul style="list-style-type: none"> • Changed datasheet with Infineon logo - all pages. • Updated datasheet based on IFX template. • Removed "HEXFET® Power MOSFET" added "IR MOSFET™" -page1 • Corrected TO-220 Package outline on page 8. • Added disclaimer on last page.

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